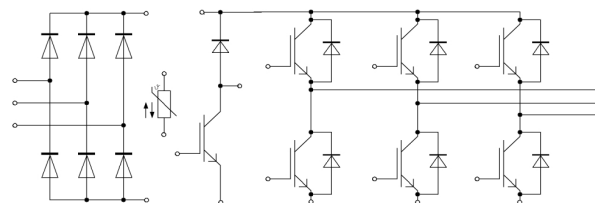
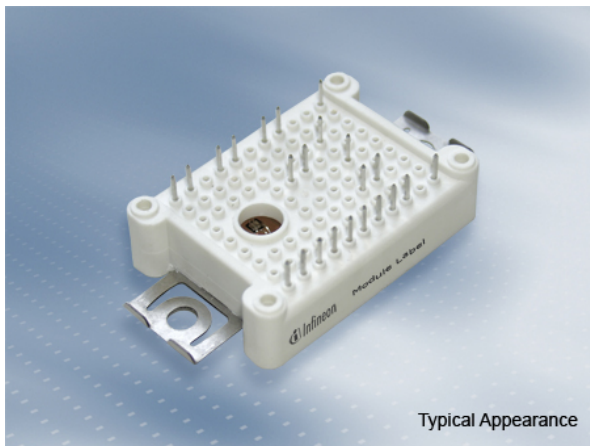


EasyPIM™ 模块 采用第四代沟槽栅/场终止IGBT4和第四代发射极控制二极管 带有温度检测NTC
EasyPIM™ module with Trench/Fieldstop IGBT4 and Emitter Controlled 4 diode and NTC

初步数据 / Preliminary Data



$V_{CES} = 1200V$
 $I_{C\ nom} = 15A / I_{CRM} = 30A$

典型应用

- 辅助逆变器
- 空调
- 电机传动

Typical Applications

- Auxiliary Inverters
- Air Conditioning
- Motor Drives

电气特性

- 低开关损耗
- 沟槽栅IGBT4
- V_{CEsat} 带正温度系数
- 低 V_{CEsat}

Electrical Features

- Low Switching Losses
- Trench IGBT 4
- V_{CEsat} with positive Temperature Coefficient
- Low V_{CEsat}

机械特性

- 低热阻的三氧化二铝 (Al_2O_3 衬底
- 紧凑型设计
- 焊接技术
- 集成的安装夹使安装坚固

Mechanical Features

- Al_2O_3 Substrate with Low Thermal Resistance
- Compact design
- Solder Contact Technology
- Rugged mounting due to integrated mounting clamps

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: DK	date of publication: 2013-10-03	
approved by: MB	revision: 2.2	UL approved (E83335)

初步数据
Preliminary Data

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{ nom}}$ I_C	15 28	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	30	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175$	P_{tot}	130	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 15\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 15\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 15\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,85 2,15 2,25	2,25	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 0,48\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,2	5,8	6,4 V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	0,12		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,0		Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	0,89		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,03		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 39\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ on}}$	0,055 0,055 0,055		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 39\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,059 0,065 0,065		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 39\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ off}}$	0,195 0,275 0,28		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 39\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,145 0,19 0,215		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}, L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 550\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 39\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	1,30 1,75 1,95		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}, L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3500\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 39\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	0,83 1,20 1,35		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CE\text{ max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\text{ }\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	55		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}	1,05	1,15	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	1,05		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

prepared by: DK

date of publication: 2013-10-03

approved by: MB

revision: 2.2

初步数据
Preliminary Data

二极管, 逆变器 / Diode, Inverter
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	15	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	30	A
I_{2t} -值 I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	16,0 14,0	A^2s A^2s

特征值 / Characteristic Values

				min.	typ.	max.	
正向电压 Forward voltage	$I_F = 15\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 15\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 15\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F		2,00 2,10 2,10	2,65	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 15\text{ A}, -di_F/dt = 550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}		13,0 12,0 12,0		A A A
恢复电荷 Recovered charge	$I_F = 15\text{ A}, -di_F/dt = 550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r		1,20 2,05 2,40		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 15\text{ A}, -di_F/dt = 550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}		0,37 0,68 0,80		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		1,75	1,90	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}		1,30		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

二极管, 整流器 / Diode, Rectifier
最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1600	V
最大正向均方根电流(每芯片) Maximum RMS forward current per chip	$T_C = 80^{\circ}\text{C}$	I_{FRMSM}	30	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	$T_C = 80^{\circ}\text{C}$	I_{RMSM}	30	A
正向浪涌电流 Surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I_{FSM}	300 245	A A
I_{2t} -值 I^2t - value	$t_p = 10\text{ ms}, T_{vj} = 25^{\circ}\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	450 300	A^2s A^2s

特征值 / Characteristic Values

				min.	typ.	max.	
正向电压 Forward voltage	$T_{vj} = 150^{\circ}\text{C}, I_F = 15\text{ A}$		V_F		0,85		V
反向电流 Reverse current	$T_{vj} = 150^{\circ}\text{C}, V_R = 1600\text{ V}$		I_R		1,00		mA
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		1,20	1,35	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}		1,15		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

prepared by: DK	date of publication: 2013-10-03
approved by: MB	revision: 2.2

初步数据
Preliminary Data

IGBT, 制动-斩波器 / IGBT, Brake-Chopper

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{ nom}}$ I_C	15 28	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	30	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175$	P_{tot}	130	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 15\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 15\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 15\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	1,85 2,15 2,25	2,25	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 0,48\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,2	5,8	6,4 V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	0,12		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,0		Ω
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	0,89		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	0,03		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 43\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ on}}$	0,065 0,065 0,065		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 43\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,06 0,065 0,065		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 43\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{d\text{ off}}$	0,21 0,28 0,285		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 43\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,17 0,20 0,225		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}, L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 43\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	1,35 1,80 2,00		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}, L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 43\text{ }\Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	0,85 1,20 1,35		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CE\text{ max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\text{ }\mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	55		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}	1,05	1,15	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1\text{ W/(m}\cdot\text{K)}$		R_{thCH}	1,05		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

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revision: 2.2

初步数据
Preliminary Data

二极管，制动-斩波器 / Diode, Brake-Chopper

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	10	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	20	A
I_{2t} -值 I_{2t} - value	$V_R = 0\text{ V}$, $t_P = 10\text{ ms}$, $T_{vj} = 125^{\circ}\text{C}$	I_{2t}	16,0	A ² s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 10\text{ A}$, $V_{GE} = 0\text{ V}$ $I_F = 10\text{ A}$, $V_{GE} = 0\text{ V}$ $I_F = 10\text{ A}$, $V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,75 1,75 1,75	2,25	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 10\text{ A}$, $-di_F/dt = 500\text{ A}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	12,0 10,0 8,00		A A A
恢复电荷 Recovered charge	$I_F = 10\text{ A}$, $-di_F/dt = 500\text{ A}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	0,90 1,70 1,90		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 10\text{ A}$, $-di_F/dt = 500\text{ A}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) $V_R = 600\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	0,24 0,52 0,59		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}	1,75	1,90	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	1,30		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	$T_C = 25^{\circ}\text{C}$	R_{25}		5,00		k Ω
R100 偏差 Deviation of R100	$T_C = 100^{\circ}\text{C}$, $R_{100} = 493\text{ }\Omega$	$\Delta R/R$	-5		5	%
耗散功率 Power dissipation	$T_C = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

根据应用手册标定

Specification according to the valid application note.

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初步数据
Preliminary Data

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min	V _{ISOL}	2,5	kV
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃	
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		11,5 6,3	mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		10,0 5,0	mm
相对电痕指数 Comperative tracking index		CTI	> 200	
杂散电感,模块 Stray inductance module		L _{sCE}	min. 30	typ. max. nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	T _c = 25°C, 每个开关 / per switch	R _{CC'+EE'} R _{AA'+CC'}	8,00 6,00	mΩ
最大结温 Maximum junction temperature	逆变器,制动-斩波器 / inverter, brake-chopper 整流器 / rectifier	T _{vj max}		175 °C 150 °C
在开关状态下温度 Temperature under switching conditions	逆变器,制动-斩波器 / inverter, brake-chopper 整流器 / rectifier	T _{vj op}	-40 -40	150 °C 150 °C
储存温度 Storage temperature		T _{stg}	-40	125 °C
Anpresskraft für mech. Bef. pro Feder mounting force per clamp		F	20	- 50 N
重量 Weight		G	24	g

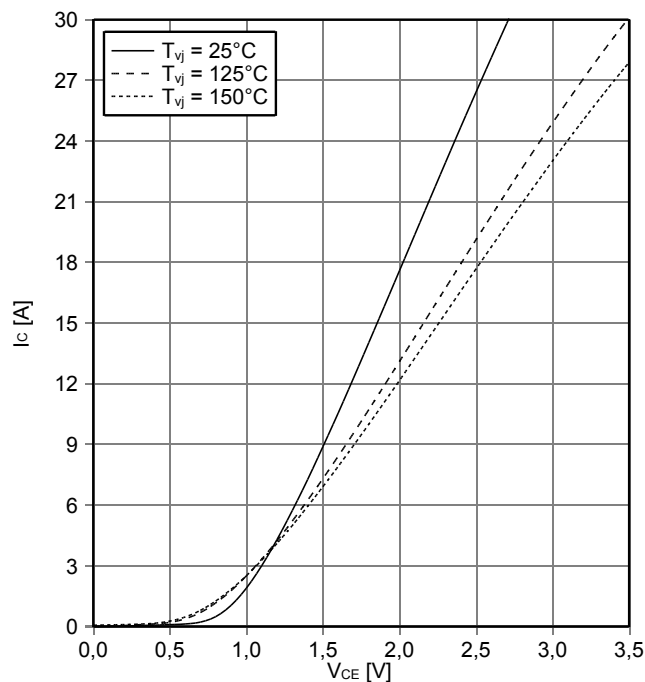
Der Strom im Dauerbetrieb ist auf 30A effektiv pro Anschlusspin begrenzt.
The current under continuous operation is limited to 30A rms per connector pin.

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初步数据
Preliminary Data

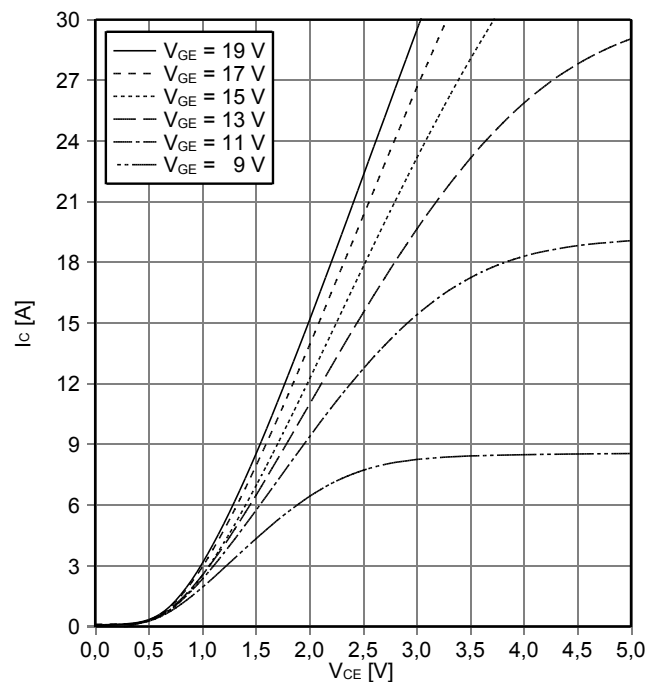
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15 \text{ V}$



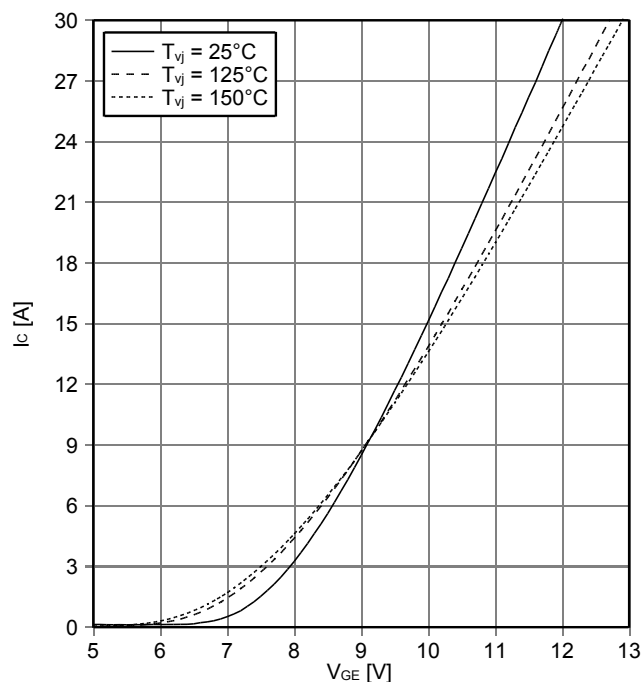
输出特性 IGBT, 逆变器 (典型)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



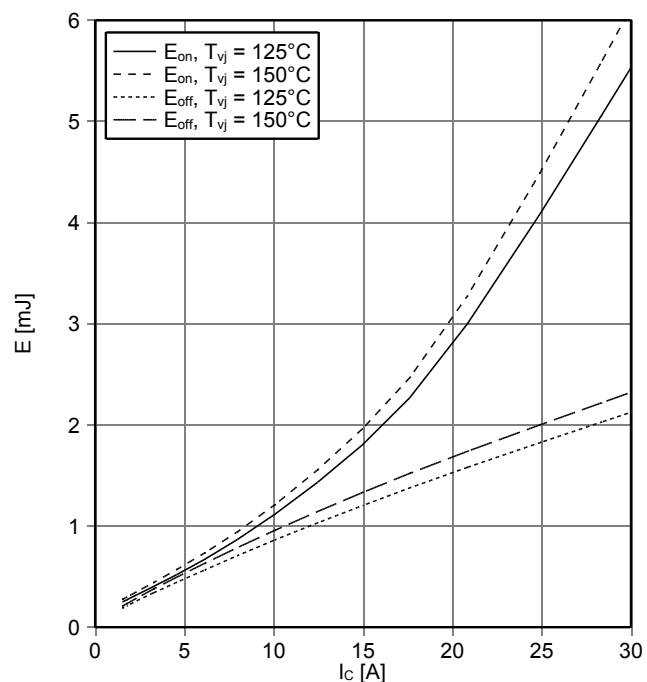
传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20 \text{ V}$



开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

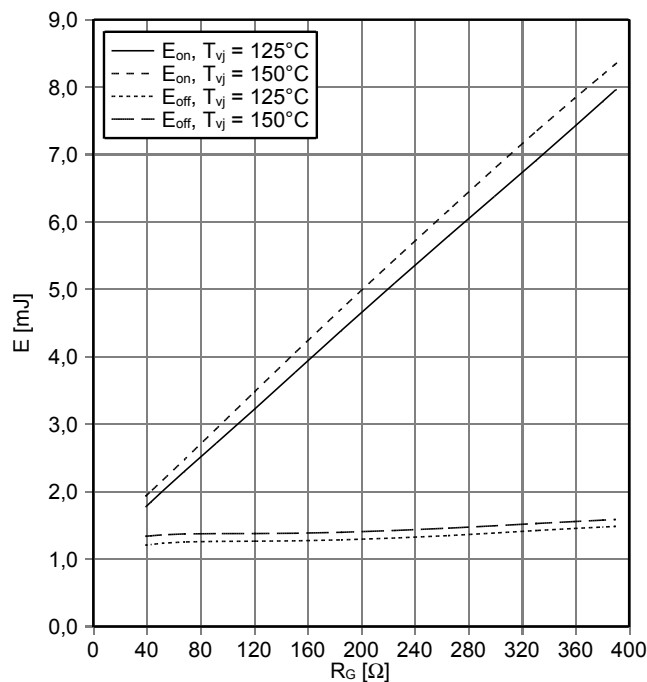
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Gon} = 39 \Omega$, $R_{Goff} = 39 \Omega$, $V_{CE} = 600 \text{ V}$



初步数据
Preliminary Data

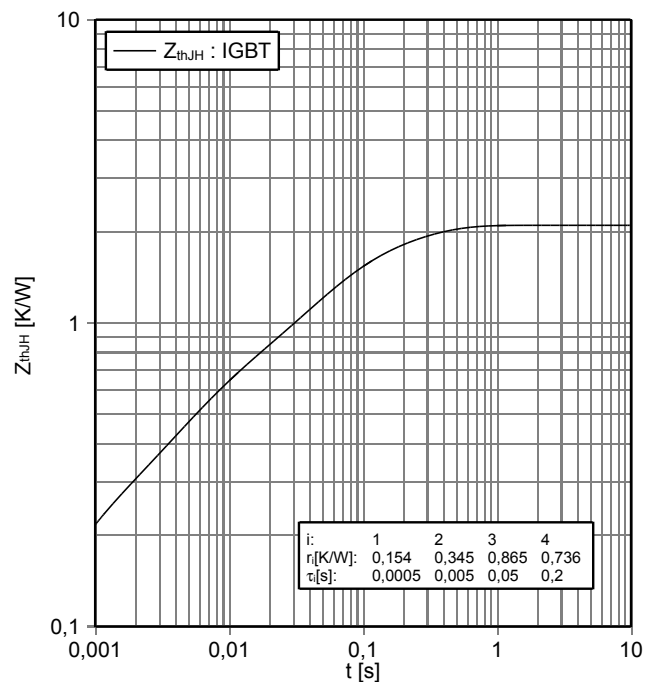
开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}$, $I_C = 15 \text{ A}$, $V_{CE} = 600 \text{ V}$



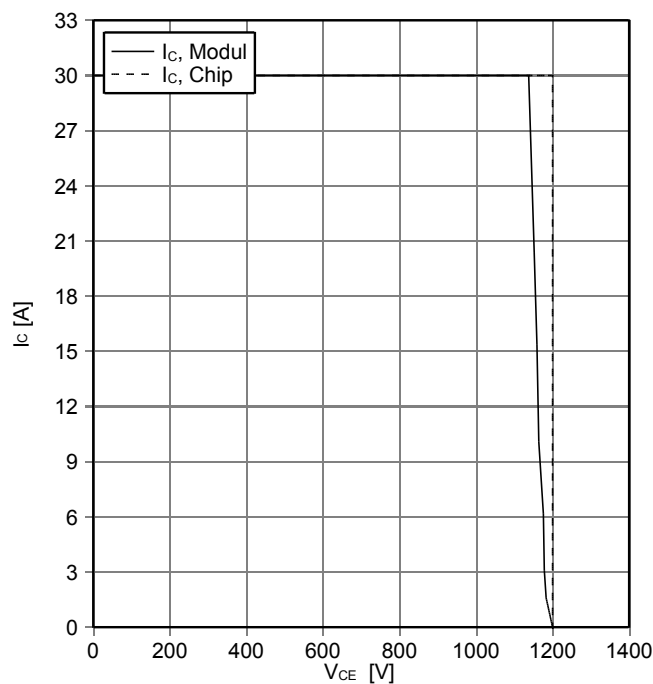
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter

$Z_{thJH} = f(t)$



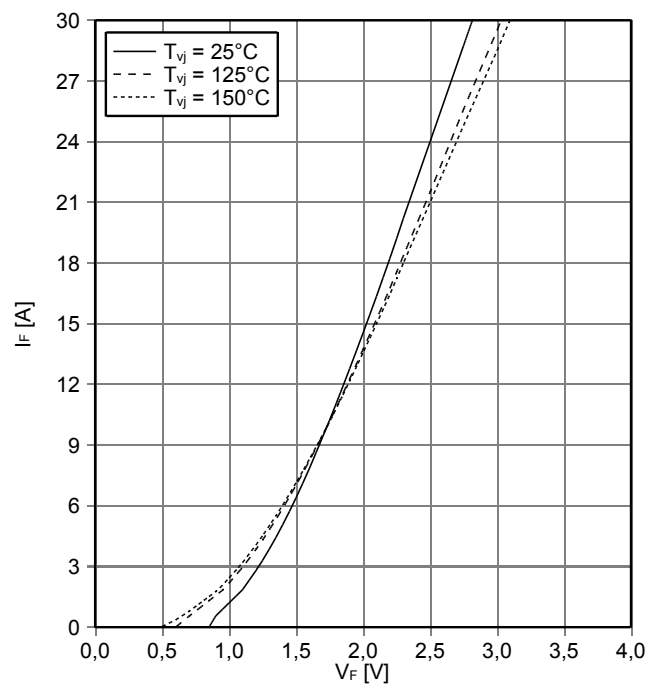
反偏安全工作区 IGBT, 逆变器 (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 39 \Omega$, $T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, 逆变器 (典型)
forward characteristic of Diode, Inverter (typical)

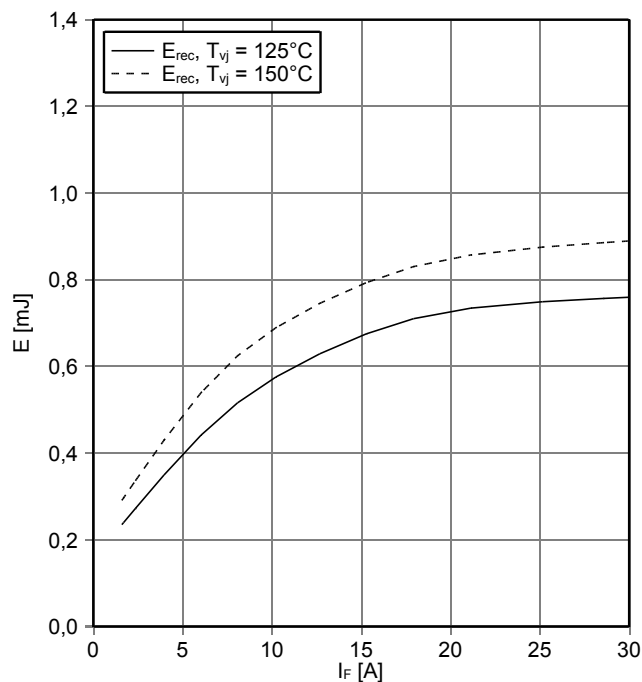
$I_F = f(V_F)$



初步数据
Preliminary Data

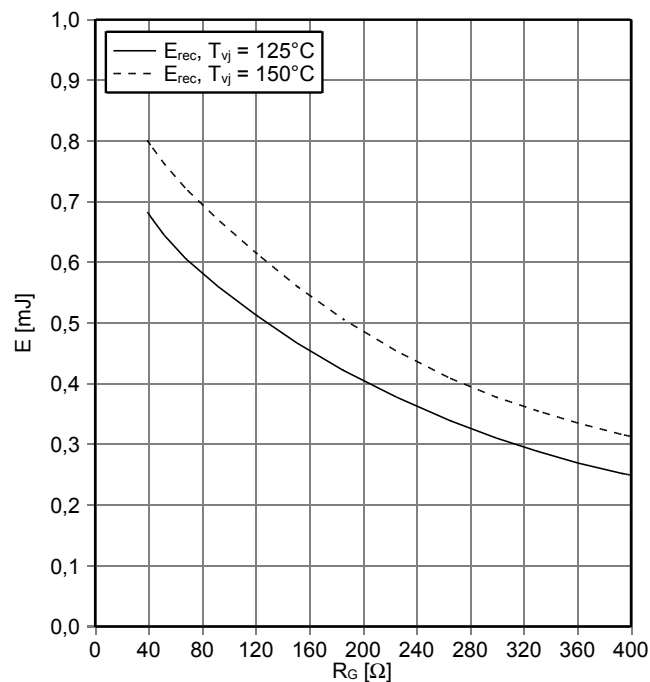
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 39 \Omega$, $V_{CE} = 600 V$



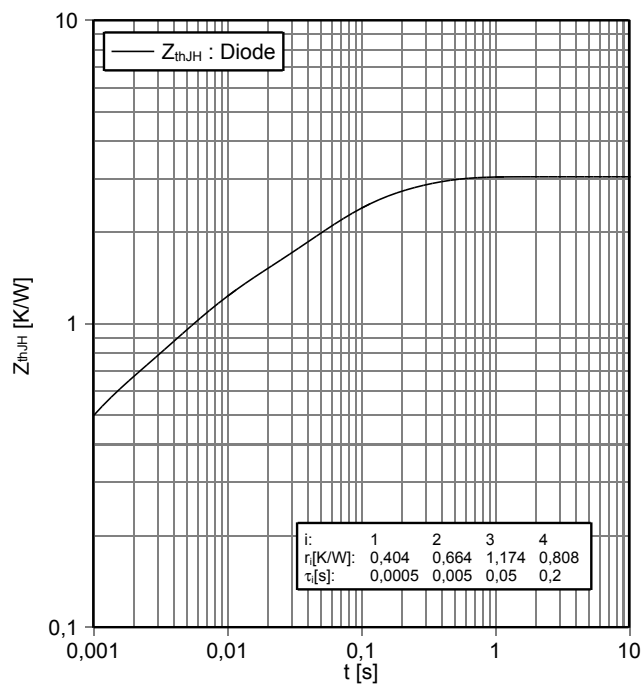
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 15 A$, $V_{CE} = 600 V$



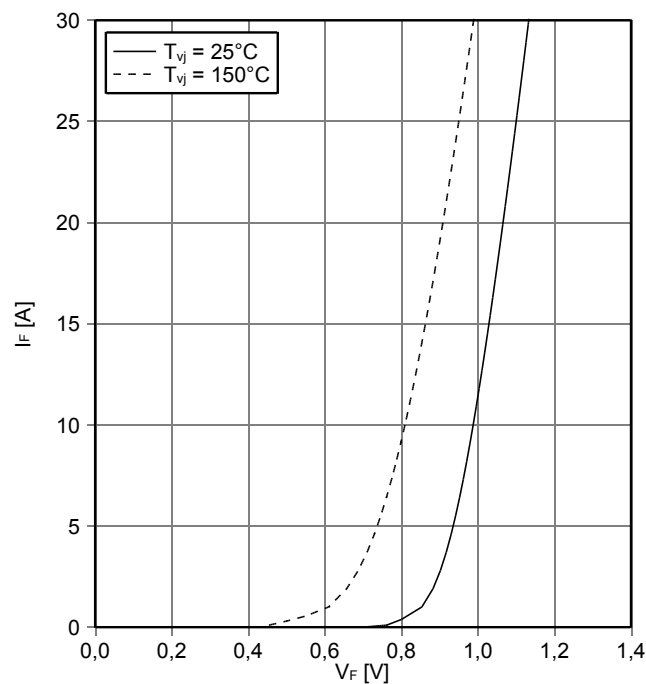
瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter

$Z_{thJH} = f(t)$



正向偏压特性 二极管,整流器 (典型)
forward characteristic of Diode, Rectifier (typical)

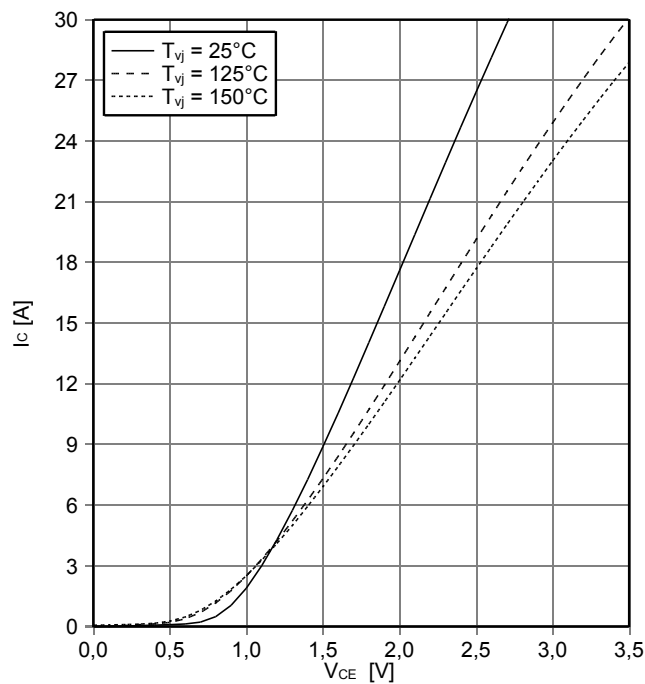
$I_F = f(V_F)$



初步数据
Preliminary Data

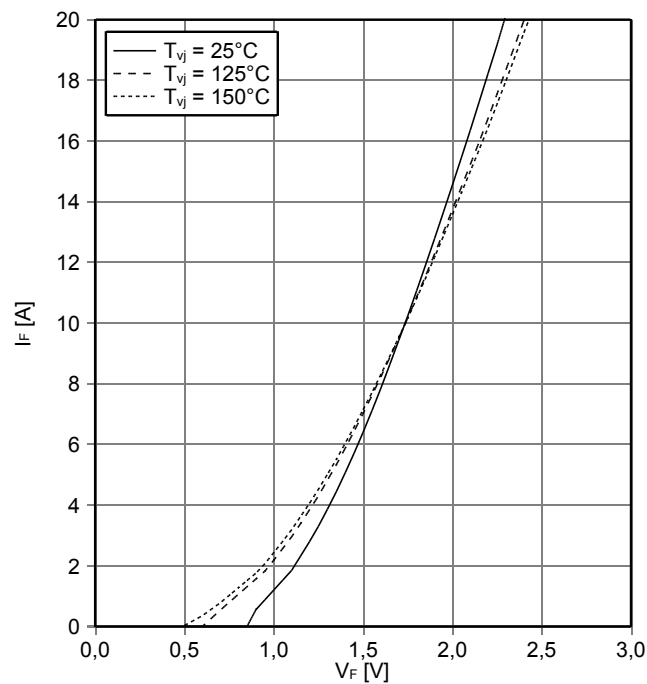
输出特性 IGBT, 制动-斩波器 (典型)
output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



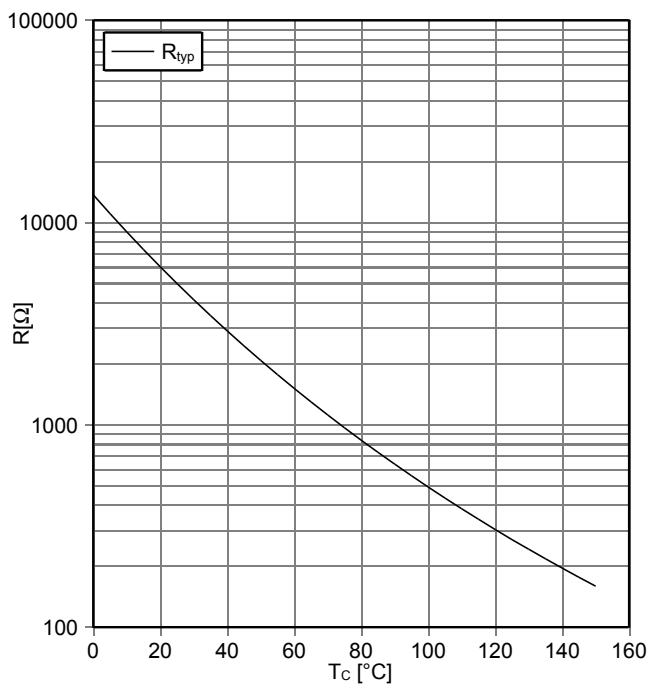
正向偏压特性 二极管, 制动-斩波器 (典型)
forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$

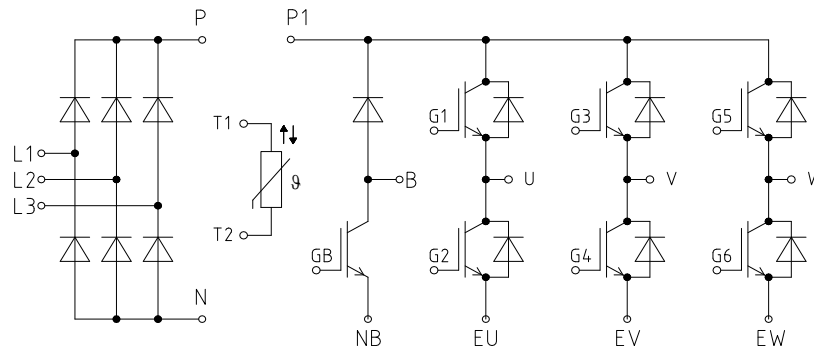


负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)

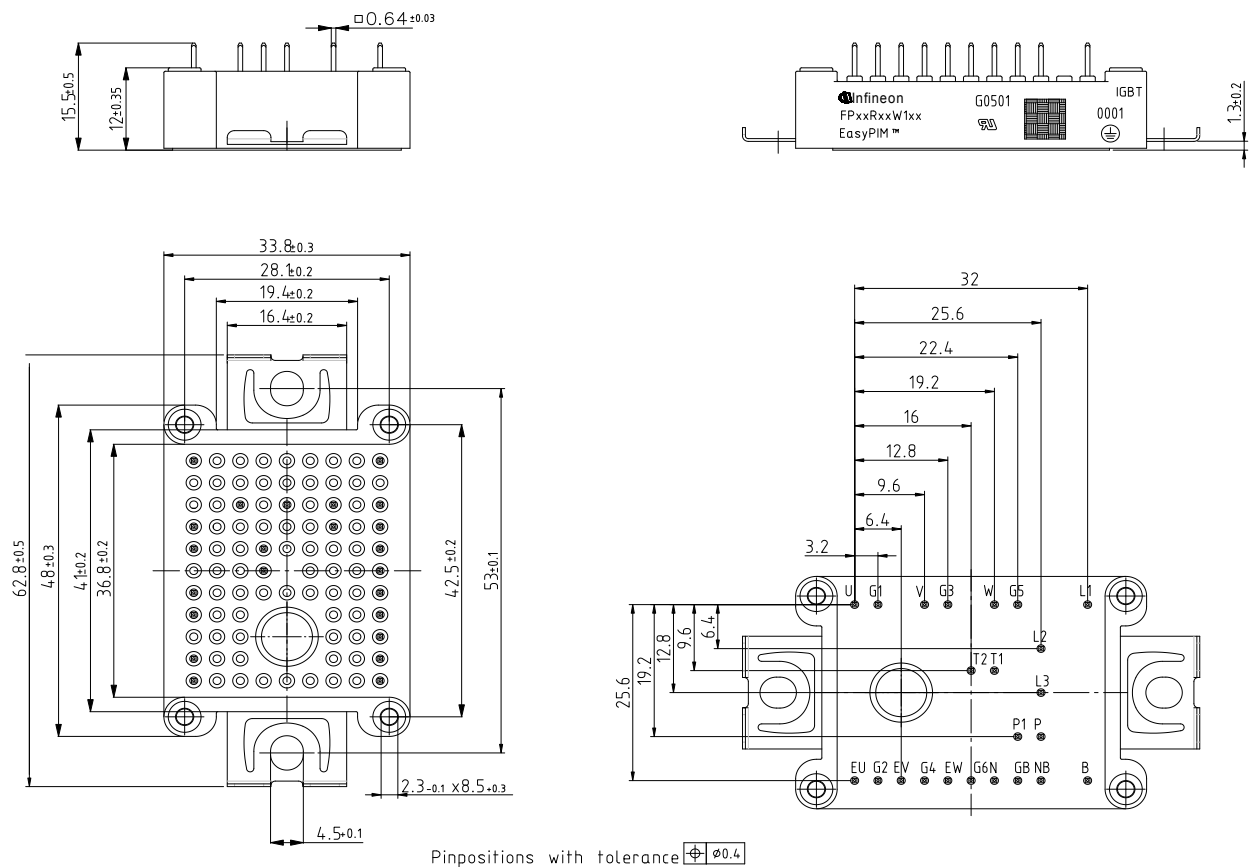
$R = f(T)$



接线图 / circuit_diagram_headline



封装尺寸 / package outlines



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初步数据 Preliminary Data

使用条件和条款

使用条件和条款

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-得到质量协议的结论

-建立联合的测试和出厂产品检查，我们可以根据测试的实际情况供货

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- to perform joint Risk and Quality Assessments;

- the conclusion of Quality Agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery depended on the realization of any such measures.

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